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PAGE 2

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YO998426DIV

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Chan et al.

Serial No.: 10/051,562

Group Art Unit: 2822

Filed: January 18, 2002

Examiner: Novacek, Christy L.

For: SELF-ALIGNED DOUBLE-GATE MOSFET BY SELECTIVE EPITAXY
AND SILICON WAFER BONDING TECHNIQUES

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Commissioner for Patents
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AMENDMENT UNDER 37 C.F.R. §1.116

Sir:

In response to the Office Action mailed July 23, 2003, please amend the above-identified patent application as follows:

IN THE CLAIMS:

Please cancel claim 36 and amend the remaining claims as follows.

99/39/2003 AFORD1 00000001 500510 10051562

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CERTIFICATE OF TRANSMISSION BY FACSIMILE (37 CFR 1.8)

Applicant(s): Chan et al.

Docket No.

YO998426DIV

Serial No.
10/051,562Filing Date
January 18, 2002Examiner
Novacek, Christy L.Group Art Unit
2822**Invention: SELF-ALIGNED COUPLE-GATE MOSFET BY SELECTIVE EPITAXY AND SILICON WAFER
BONDING TECHNIQUES**

I hereby certify that this

Amendment Under 37 C.F.R. 1.116

(Identify type of correspondence)

is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. 703-872-9319)

on **September 23, 2003**
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